

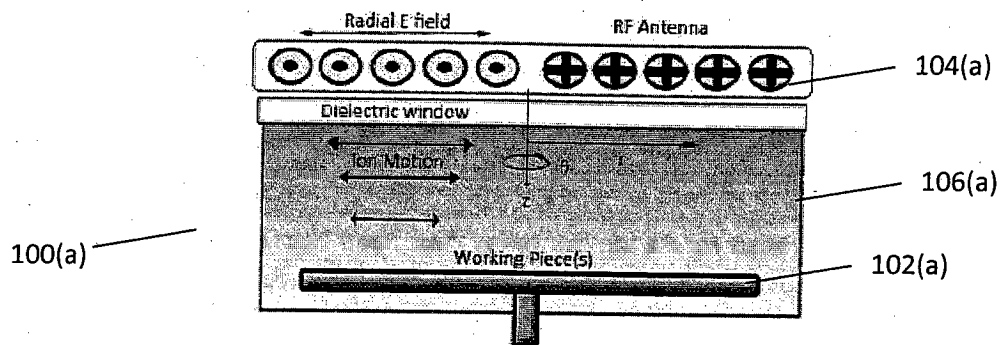


Figure 1(a)

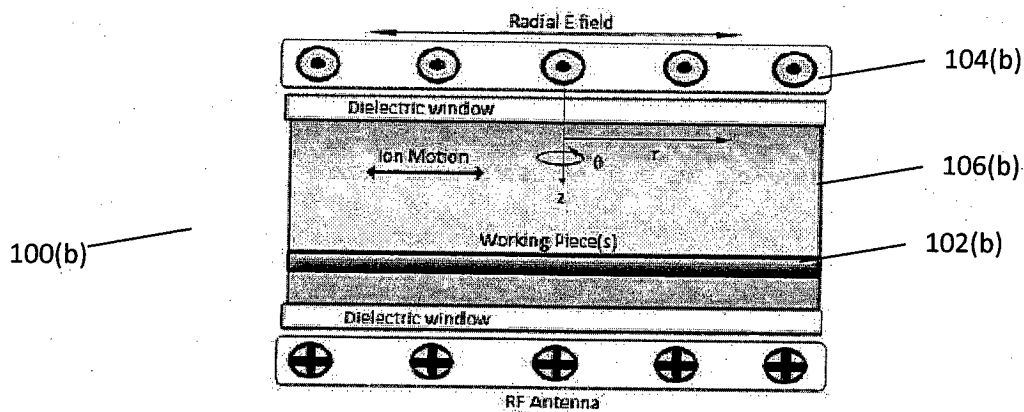


Figure 1(b)

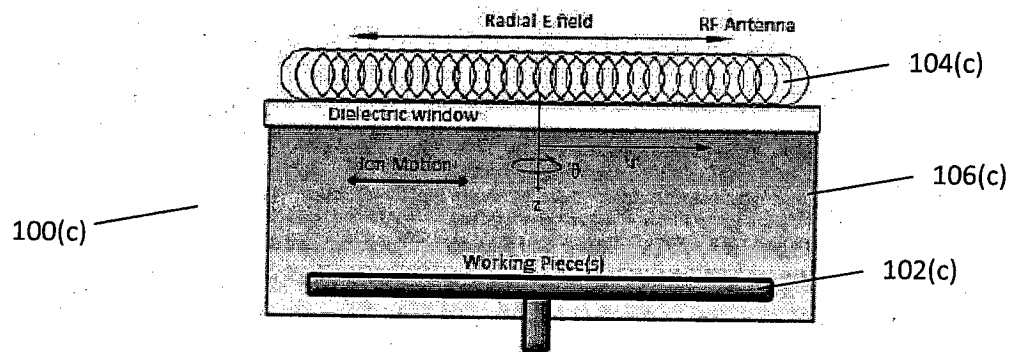


Figure 1(c)

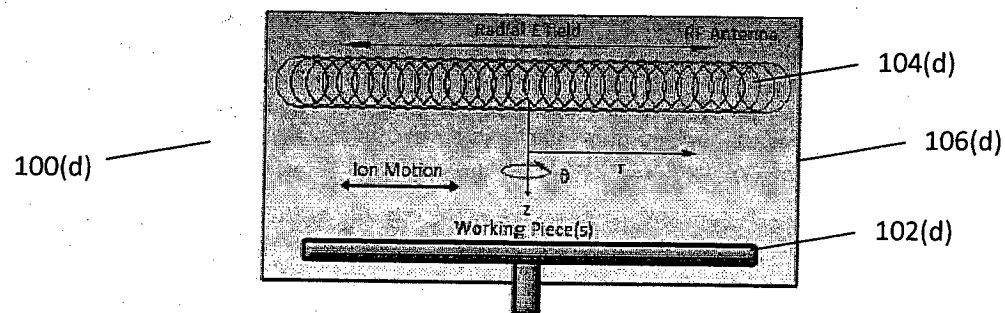


Figure 1(d)

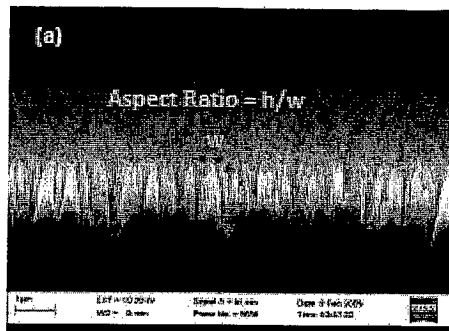


Figure 2



Figure 3

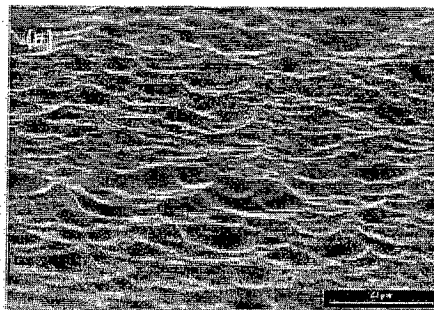


Figure 4

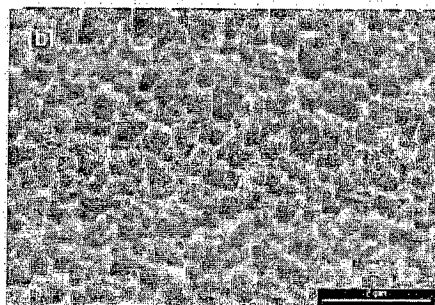


Figure 5

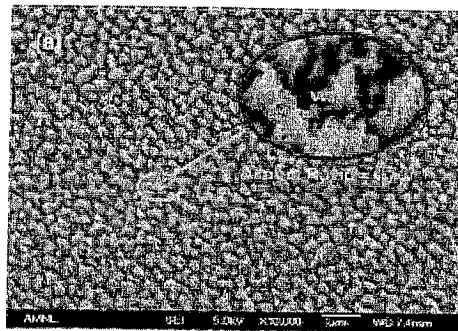


Figure 6

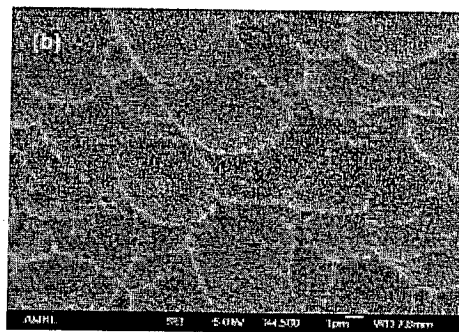


Figure 7

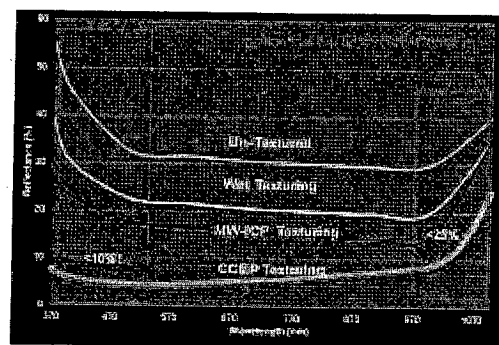


Figure 8

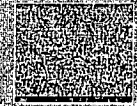
	Alkaline	Acidic	MW-ICP	CCCP
(a) Textured Profile				
(b) KPI of Texturing				
1. Textured surfaces	Double	Double	Single	Single
2. Residue removal (LID problem)	Complete	Incomplete	Nil	Nil
3. Light reflectance	20-40%	20-40%	15-40%	1-25%
4. Aspect ratio of textured profile	Medium	Medium	High	Low
5. Surface damage	Low	Low	High	Low
(c) Industrial Concerns				
1. Wafer/Water/Chemical Wastage	High	High	Nil	Nil
2. Silicon Type	Mono-	Multi-	Mono/Multi-	Mono/Multi-
3. Equipment Footprint	>20 Meters	>20 Meters	<5 Meters	<5 Meters

Figure 9

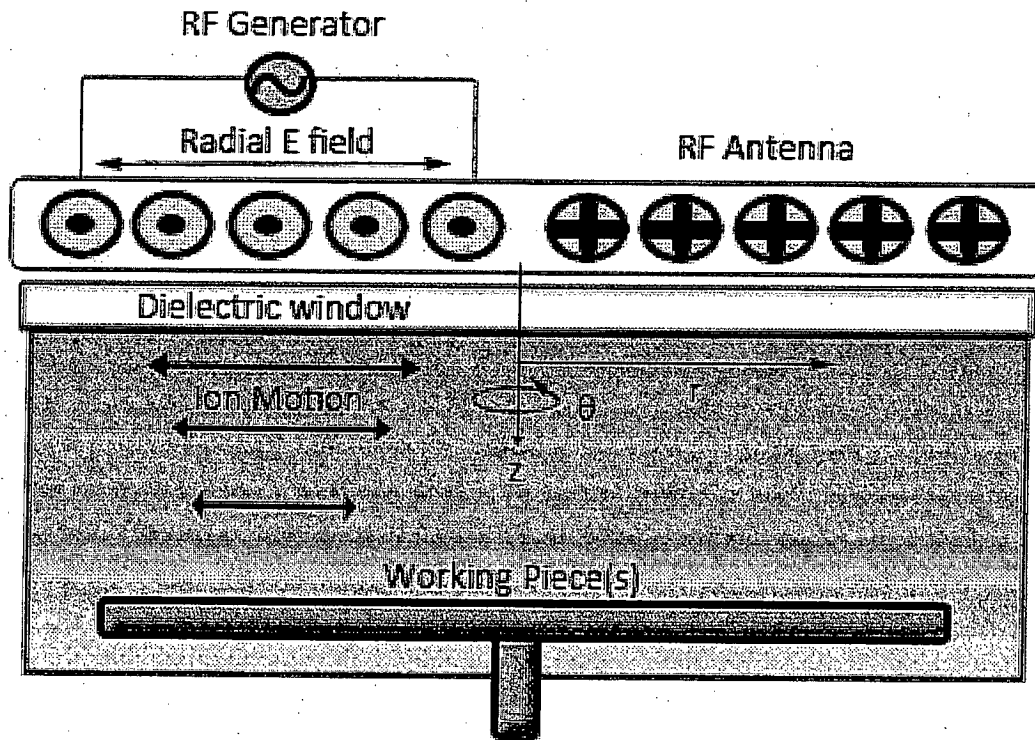


Figure 10(a)

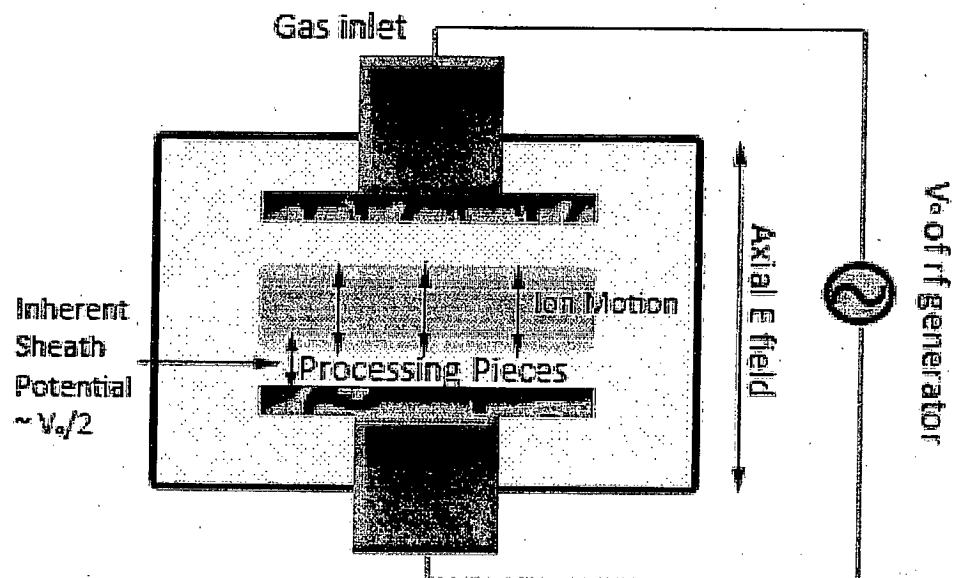


Figure 10(b)

Process Parameter	Value
RF input power	100 W – 1000 W
Working Pressure	1 Pa – 100 Pa
Gas Ratio of SiH ₄ :H ₂	1:1 to 1:10
Substrate Temperature	Room Temperature to 250 °C

Figure 11

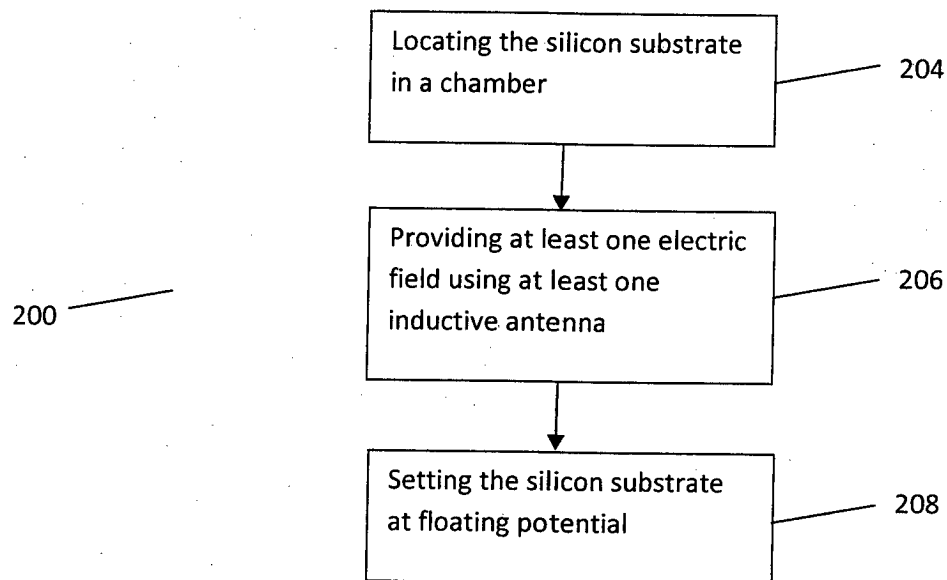


Figure 12